AMENDMENTS TO THE SPECIFICATION

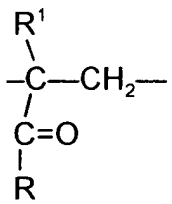
Please amend the specification in the below-indicated manner.

Please replace the paragraph beginning at page 5, line 15 with the following rewritten paragraph:

Lactic acid polymers and lactic acid copolymers may be made from monomers of lactic acid and optionally modifying monomers such as glycols, specifically ethylene glycol and propylene glycol, p-dioxanone, ~~1,5-dioxepan-2-one,~~ 1,5-dioxepan-2-one, 1,4-oxathialan-2-one, ~~4,4-dioxide~~ and various mixtures and blends thereof. For example, lactic acid copolymers may be a blend of polylactic acid and ~~polyethylene~~ polyethylene oxide. In one embodiment, the lactic acid polymers and copolymers contain from about 50% to about 100% by weight of lactic acid monomers and from about 0% to about 50% by weight of the modifying polymer. In another embodiment, the lactic acid polymers and copolymers contain from about 60% to about 98% by weight of lactic acid monomers and from about 2% to about 40% by weight of the modifying polymer.

Please replace the paragraph beginning at page 6, line 1 with the following rewritten paragraph:

Polymers and copolymers containing side chain ketone groups can be made by incorporating a ketone into a polymer. The desired structure which is to be included in the polymer backbone is of the form:



where R is an alkyl, cycloalkyl, aryl, alkenyl, or alkaryl group containing from one to

about 10 carbon atoms and R^1 is hydrogen or an alkyl, cycloalkyl, aryl, or alkaryl group containing from one to about 7 carbon atoms. In vinyl resins, R is an alkyl or aryl group containing from one to about 9 carbon atoms and R^1 is hydrogen or an alkyl group containing from one to about 7 carbon atoms.

Please amend the Abstract in the below-indicated manner.

Please amend the Abstract on page 28 in the following manner:

~~One aspect of the present invention relates to a semiconductor structure, containing a semiconductor substrate; a resist over the semiconductor substrate; and a light-degradable surface coupling agent between the resist and the semiconductor substrate. Another aspect of the present invention relates to a method~~ Disclosed are methods of processing a semiconductor structure, involving the steps of depositing a light-degradable surface coupling agent on a semiconductor substrate; depositing a resist over the light-degradable surface coupling agent; irradiating portions of the resist, wherein the light-degradable surface coupling agent under the irradiated portions of the resist at least partially decomposes; and developing the resist. ~~Yet another aspect of the present invention relates to a semiconductor processing system, containing a processing chamber operable to form a light-degradable surface coupling agent layer on a substrate in the chamber; a supply of a light-degradable surface coupling agent; and a measurement system for in situ measuring a thickness of the light-degradable surface coupling agent layer being formed and for providing a measurement signal indicative of the measured thickness.~~

Attachment: Replacement Sheet with New Abstract